

National Semiconductor is now part of
Texas Instruments.

Search <http://www.ti.com/> for the latest technical
information and details on our current products and services.

LM48413 Boomer® Audio Power Amplifier Series

Ultra Low EMI, Filterless, 1.2W Stereo Class D Audio Power Amplifier with E²S and National 3D Enhancement

General Description

The LM48413 is a single supply, high efficiency, 1.2W/channel, filterless switching audio amplifier. The LM48413 features National's Enhanced Emissions Suppression (E²S) system - a unique patented ultra low EMI, spread spectrum, PWM architecture. It significantly reduces RF emission while preserving audio quality and efficiency. The E²S system improves battery life, reduces external component count, board area consumption, system cost and product design cycle time. The LM48413TL is available in a micro-SMD package, further saving space.

The LM48413 is designed to meet the demands of mobile phones and other portable communication devices. Operating from a single 5V supply, the device is capable of delivering 1.2W/channel of continuous output power to a 8Ω load with less than 1% THD+N. Flexible power supply requirements allow operation from 2.4V to 5.5V. The wide band spread spectrum architecture of the LM48413 reduces EMI-radiated emissions due to the modulator frequency.

The LM48413 features high efficiency compared with conventional Class AB amplifiers. The E²S system includes an advanced, patent-pending edge rate control (ERC) architecture that further reduce emissions by minimizing the high frequency components of the device output, while maintaining its high quality audio reproduction and high efficiency ($\eta = 85\%$ at $V_{DD} = 3.6V$, $P_O = 500mW$). The LM48413 also includes National's 3D audio enhancement that improves stereo sound quality. In devices where the left and right speakers are in close proximity, 3D enhancement affects channel specialization, widening the perceived soundstage.

Output short circuit protection prevents the device from being damaged during fault conditions. Superior click and pop suppression eliminates audible transients on power up/down and during shutdown. Shutdown control also provided to maximize power savings.

Key Specifications

■ Quiescent Power Supply Current at 3.6V supply	4mA (typ)
■ Power Output at $V_{DD} = 5V$, $R_L = 8\Omega$, THD $\leq 1\%$	1.2W (typ)
■ Shutdown current	0.03μA (typ)
■ Efficiency at 3.6V, 100mW into 8Ω	80% (typ)
■ Efficiency at 3.6V, 500mW into 8Ω	85% (typ)
■ Efficiency at 5V, 1W into 8Ω	86% (typ)

Features

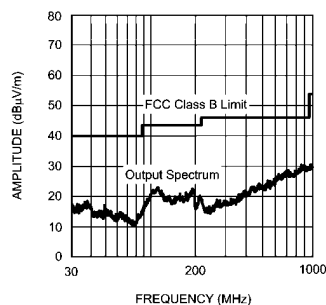
- E²S system reduces EMI preserving audio quality and efficiency
- Output Short Circuit Protection
- Stereo Class D operation
- No output filter required
- National 3D Enhancement
- Minimum external components
- Click and Pop suppression
- Micro-power shutdown
- Available in space-saving approximately 2mm x 2.2mm micro SMD package

Applications

- Mobile phones
- PDAs
- Laptops

EMI Plot Using 6 inch Speaker Cables

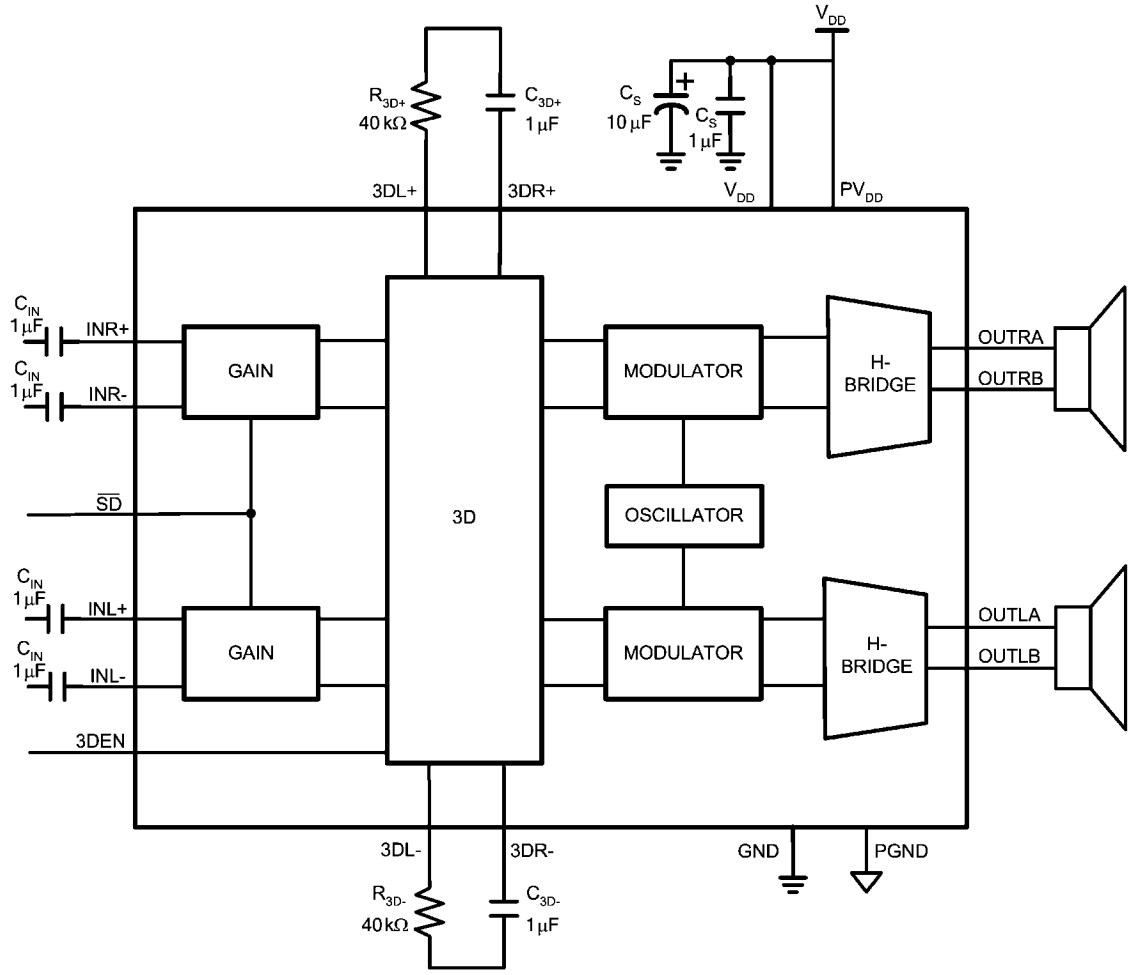
EMI Radiation vs Frequency
 $V_{DD} = 3V$, $R_L = 15\mu H + 8\Omega + 15\mu H$



30063536

Boomer® is a registered trademark of National Semiconductor Corporation.

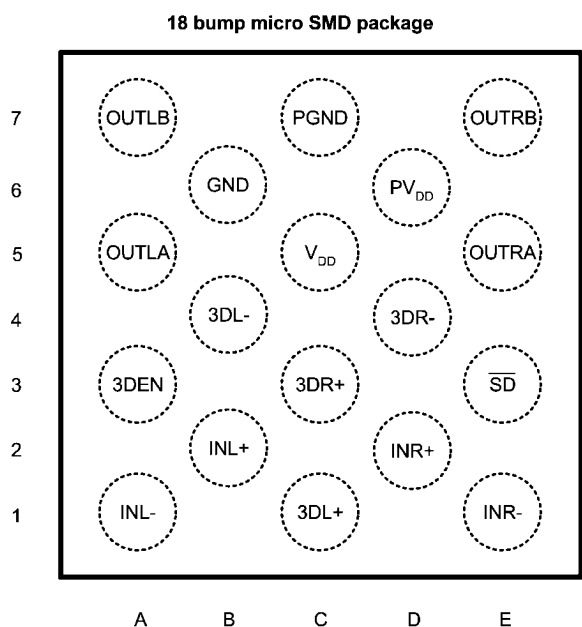
Typical Application



30063541

FIGURE 1. Typical Audio Amplifier Application Circuit

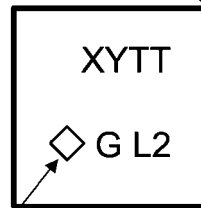
Connection Diagrams



30063538

Top View
Order Number LM48413TL
See NS Package Number TLA18CBA

micro SMD Marking



Bump A1 Mark

30063539

Top View
XY = 2 Digit date code
TT = Die Traceability
G = Boomer Family
L2 = LM48413TL

Ordering Information

Order Number	Package	Package DWG #	Transport Media	MSL Level	Green Status
LM48413TL	18 Bump micro SMD	TLA18CBA	250 units on tape and reel	1	RoHS & no Sb/Br
LM48413TLX	18 Bump micro SMD	TLA18CBA	3000 units on tape and reel	1	RoHS & no Sb/Br

Bump Descriptions

Bump	Name	Description
A1	INL-	Left Channel Inverting Input
A3	3DEN	3D Enable Input
A5	OUTLA	Left Channel Non-Inverting Output
A7	OUTLB	Left Channel Inverting Output
B2	INL+	Left Channel Non-Inverting Input
B4	3DL-	Left Channel inverting 3D connection. Connect to 3DR- through C_{3D-} and R_{3D-} .
B6	GND	Ground
C1	3DL+	Left Channel non-inverting 3D connection. Connect to 3DR+ through C_{3D+} and R_{3D+} .
C3	3DR+	Right Channel non-inverting 3D connection. Connect to 3DL+ through C_{3D+} and R_{3D+} .
C5	V_{DD}	Power Supply. Connect to PV_{DD} supplying same voltage.
C7	PGND	Power Ground
D2	INR+	Right Channel Non-inverting Input
D4	3DR-	Right Channel inverting 3D connection. Connect to 3DL- through C_{3D-} and R_{3D-} .
D6	PV_{DD}	Amplifier Power Supply
E1	INR-	Right Channel Inverting Input
E3	\overline{SD}	Connect to GND for disabling the device. Connect to V_{DD} for normal operation.
E5	OUTRA	Right Channel Non-inverting Output
E7	OUTRB	Right Channel Inverting Output

Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (Note 1)	6.0V
Storage Temperature	-65°C to +150°C
Input Voltage	-0.3V to $V_{DD} + 0.3V$
Power Dissipation (Note 3)	Internally Limited
ESD Rating (Note 4)	2000V
ESD Rating (Note 5)	200V

Junction Temperature	150°C
Thermal Resistance	
θ_{JA}	47°C/W

Operating Ratings (Notes 1, 2)

Temperature Range	
$T_{MIN} \leq T_A \leq T_{MAX}$	$-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$
Supply Voltage (V_{DD} , PV_{DD})	$2.4V \leq V_{DD} \leq 5.5V$

Electrical Characteristics $V_{DD} = PV_{DD} = 3.6V$ (Notes 1, 2) The following specifications apply for $R_L = 8\Omega$ (Note 8), $f = 1\text{kHz}$, unless otherwise specified. Limits apply for $T_A = 25^\circ\text{C}$.

Symbol	Parameter	Conditions	LM48413		Units (Limits)
			Typical	Limit	
			(Note 6)	(Note 7)	
V_{OS}	Differential Output Offset Voltage	$V_{IN} = 0$, $V_{DD} = 2.4V$ to $5.0V$	3		mV
I_{DD}	Quiescent Power Supply Current	$V_{IN} = 0$, No Load, $V_{SD} = V_{DD}$, $V_{DD} = 3.6V$ $V_{DD} = 5V$	4.3 5.2	5.5 7	mA (max) mA (max)
I_{SD}	Shutdown Current	$V_{SD} = GND$	0.03	1	μA (max)
V_{IH}	Logic Input High Voltage			1.4	V (min)
V_{IL}	Logic Input Low Voltage			0.4	V (max)
T_{WU}	Wake-Up Time		4		ms
A_V	Gain		24	23.5 24.5	dB (min) dB (max)
R_{IN}	Input Resistance		20		$k\Omega$
P_O	Output Power (Per Channel)	THD $\leq 10\%$, $f = 1\text{kHz}$, 22kHz BW			
		$V_{DD} = 5V$	1.5		W
		$V_{DD} = 3.6V$	720	600	mW (min)
		$V_{DD} = 2.5V$	320		mW
		THD $\leq 1\%$, $f = 1\text{kHz}$, 22kHz BW			
		$V_{DD} = 5V$	1.2		W
		$V_{DD} = 3.6V$	600		mW
THD+N	Total Harmonic Distortion + Noise	$P_O = 500\text{mW/Ch}$, $f = 1\text{kHz}$, 22kHz BW	0.03		%
		$P_O = 300\text{mW/Ch}$, $f = 1\text{kHz}$, 22kHz BW	0.03		%
PSRR	Power Supply Rejection Ratio	$V_{RIPPLE} = 200\text{mV}_{P-P}$ Sine, Inputs AC GND, $C_{IN} = 1\mu\text{F}$, input referred $f_{RIPPLE} = 217\text{Hz}$ $f_{RIPPLE} = 1\text{kHz}$	91 90		dB dB
CMRR	Common Mode Rejection Ratio	$V_{RIPPLE} = 1V_{P-P}$ $f_{RIPPLE} = 217\text{Hz}$	72		dB
η	Efficiency	$P_O = 1\text{W/Ch}$, $f = 1\text{kHz}$, $R_L = 8\Omega$, $V_{DD} = 5V$	86		%
X_{TALK}	Crosstalk	$P_O = 500\text{mW/Ch}$, $f = 1\text{kHz}$	93		dB
SNR	Signal-to-Noise Ratio	$V_{DD} = 5V$, $P_O = 1W$	88		dB
ϵ_{OS}	Output Noise	Input referred, A-Weighted	5		μV

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the *Absolute Maximum Ratings* or other conditions beyond those indicated in the *Recommended Operating Conditions* is not implied. The *Recommended Operating Conditions* indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.

Note 2: The *Electrical Characteristics* tables list guaranteed specifications under the listed *Recommended Operating Conditions* except as otherwise modified or specified by the *Electrical Characteristics Conditions* and/or Notes. Typical specifications are estimations only and are not guaranteed.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum allowable power dissipation is $P_{DMAX} = (T_{JMAX} - T_A) / \theta_{JA}$ or the number given in *Absolute Maximum Ratings*, whichever is lower.

Note 4: Human body model, applicable std. JESD22-A114C.

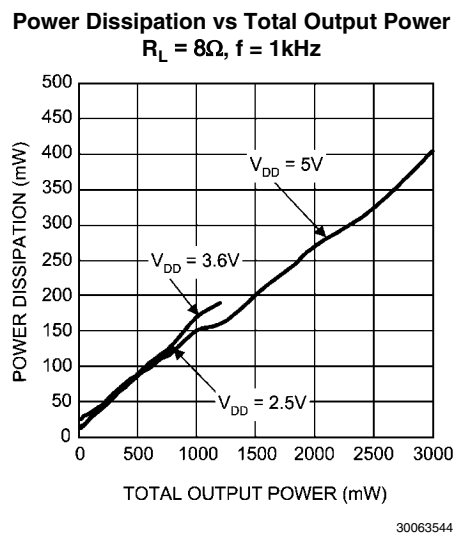
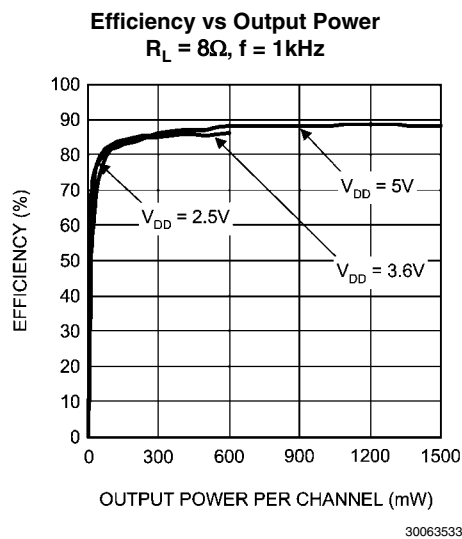
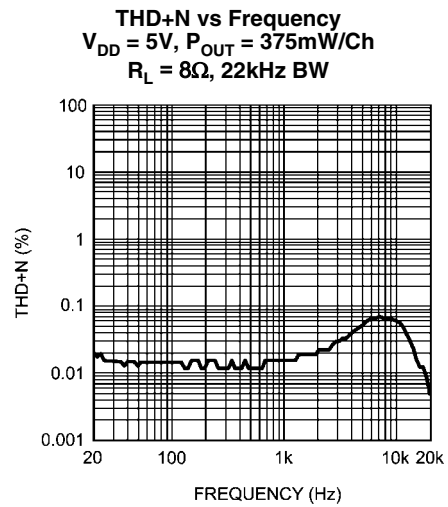
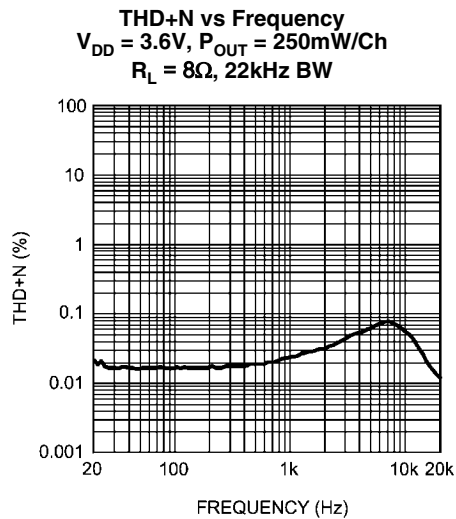
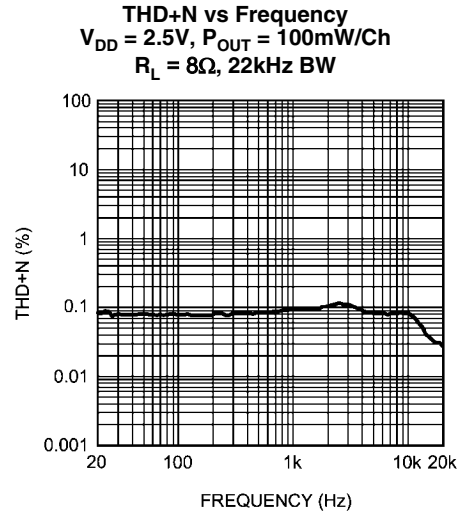
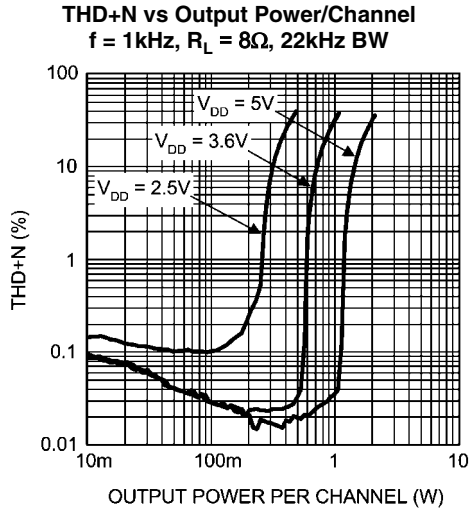
Note 5: Machine model, applicable std. JESD22-A115-A. The ESD Machine Model rating of device bump E3 = 150V.

Note 6: Typical values represent most likely parametric norms at $T_A = +25^\circ\text{C}$, and at the *Recommended Operation Conditions* at the time of product characterization and are not guaranteed.

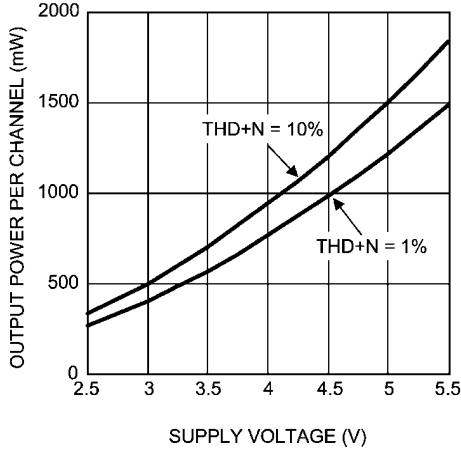
Note 7: Datasheet min/max specification limits are guaranteed by test or statistical analysis.

Note 8: R_L is a resistive load in series with two inductors to simulate an actual speaker load. For $R_L = 8\Omega$, the load is $15\mu\text{H} + 8\Omega + 15\mu\text{H}$.

Typical Performance Characteristics

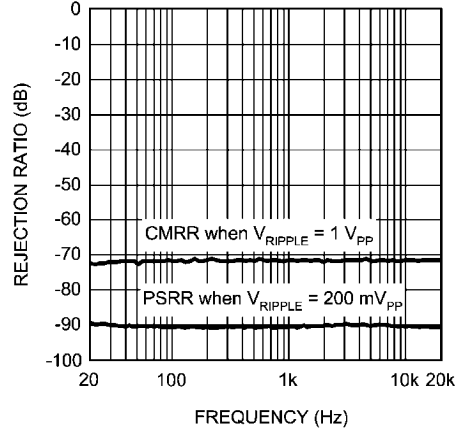


Output Power/Channel vs Supply Voltage
 $R_L = 8\Omega$, $f = 1\text{kHz}$, 22kHz BW



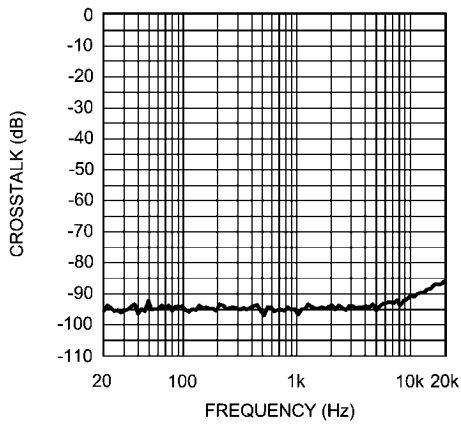
30063542

PSRR and CMRR vs Frequency
 $V_{DD} = 3.6\text{V}$, $R_L = 8\Omega$



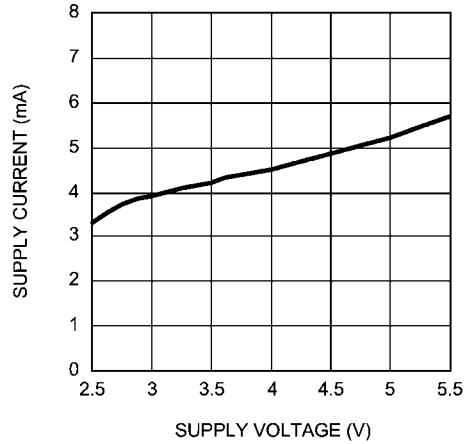
30063537

Crosstalk vs Frequency
 $V_{DD} = 3.6\text{V}$, $P_O = 500\text{mW}$, $R_L = 8\Omega$



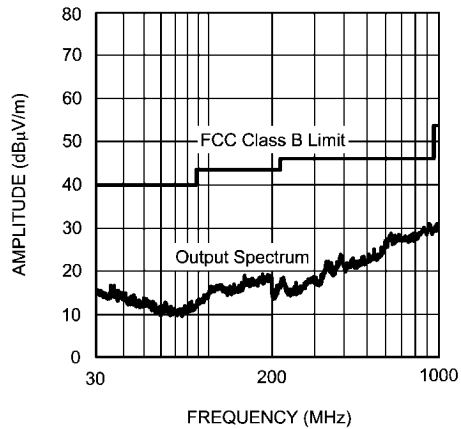
30063531

Supply Current vs Supply Voltage
 No Load



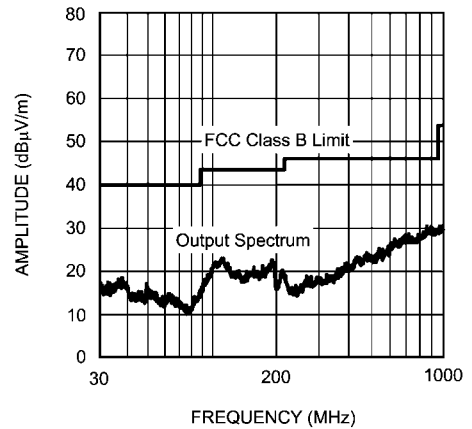
30063529

EMI Radiation vs Frequency
 $V_{DD} = 3\text{V}$, $R_L = 8\Omega$, 3 inch cables

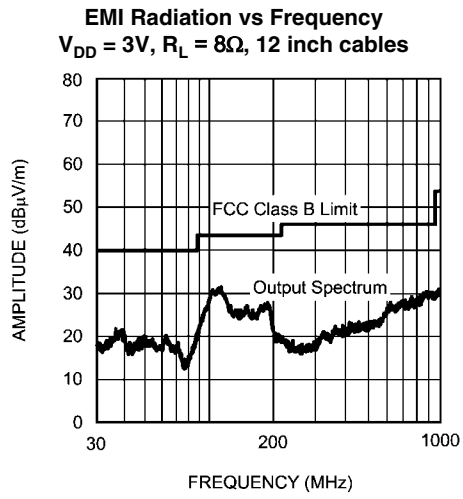


30063535

EMI Radiation vs Frequency
 $V_{DD} = 3\text{V}$, $R_L = 8\Omega$, 6 inch cables



30063536



30063534

Application Information

GENERAL AMPLIFIER FUNCTION

The LM48413 stereo Class D audio power amplifier features a filterless modulation scheme that reduces external component count, conserving board space and reducing system cost. The outputs of the device transition from PV_{DD} to GND with a 390kHz switching frequency. With no signal applied, the outputs switch with a 50% duty cycle, in phase, causing the two outputs to cancel. This cancellation results in no net voltage across the speaker, thus there is no current to the load in the idle state.

When an input signal is applied, the duty cycle (pulse width) of the LM48413 output's change. For increasing output voltage, the duty cycle of one side of each output increases, while the duty cycle of the other side of each output decreases. For decreasing output voltages, the converse occurs. The difference between the two pulse widths yields the differential output voltage.

SHUTDOWN FUNCTION

The LM48413 features a low current shutdown mode. Set $\overline{SD} = \text{GND}$ to disable the amplifier and reduce supply current to 0.03 μA .

Switch \overline{SD} between GND and V_{DD} for minimum current consumption in shutdown. The LM48413 may be disabled with shutdown voltages in between GND and V_{DD} , but the idle current will be greater than the typical value. The LM48413 shutdown input has an internal 300k Ω pull-down resistor. The purpose of this resistor is to eliminate any unwanted state changes when this pin is floating. To minimize shutdown current, it should be driven to GND or left floating. If it is not driven to GND, or floating, a small increase in shutdown supply current will be noticed.

SPREAD SPECTRUM

The LM48413 outputs are modulated in spread spectrum scheme eliminating the need for output filters, ferrite beads or chokes. During its operation, the switching frequency varies randomly by 30% about a 390kHz center frequency, reducing the wideband spectral content and improving EMI emissions radiated by the speaker and associated cables and traces. A fixed frequency class D exhibits large amounts of spectral energy at multiples of the switching frequency. The spread spectrum architecture of the LM48413 spreads the same energy over a larger bandwidth. The cycle-to-cycle variation of the switching period does not affect the audio reproduction, efficiency, or PSRR.

ENHANCED EMISSIONS SUPPRESSION SYSTEM (E²S)

The LM48413 features National's patented E²S system that further reduces EMI, while maintaining high quality audio reproduction and efficiency. The advanced edge rate control (ERC) embedded within the E²S system works simultaneously with the spread spectrum already activated. The LM48413 ERC greatly reduces the high frequency components of the output square waves by controlling the output rise and fall times, slowing the transitions to reduce RF emissions, while maximizing THD+N and efficiency performance.

DIFFERENTIAL AMPLIFIER EXPLANATION

As logic supplies continue to shrink, system designers are increasingly turning to differential analog signal handling to preserve signal to noise ratios with restricted voltage swings. The LM48413 features two fully differential speaker ampli-

fiers. A differential amplifier amplifies the difference between the two input signals. Traditional audio power amplifiers have typically offered only single-ended inputs resulting in a 6dB reduction of SNR relative to differential inputs. The LM48413 also offers the possibility of DC input coupling which eliminates the input coupling capacitors. A major benefit of the fully differential amplifier is the improved common mode rejection ratio (CMRR) over single-ended input amplifiers. The increased CMRR of the differential amplifier reduces sensitivity to ground offset related noise injection, especially important in noisy systems.

POWER DISSIPATION AND EFFICIENCY

The major benefit of a Class D amplifier is increased efficiency versus a Class AB. The efficiency of the LM48413 is attributed to the region of operation of the transistors in the output stage. The Class D output stage acts as current steering switches, consuming negligible amounts of power compared to a Class AB amplifier. Most of the power loss associated with the output stage is due to the IR loss of the MOSFET on-resistance, along with switching losses due to gate charge.

PROPER SELECTION OF EXTERNAL COMPONENTS

Power Supply Bypassing/Filtering

Proper power supply bypassing is important for low noise performance and high PSRR. Place the 1 μF supply bypass capacitor as close to the device as possible. Traditionally, a pair of bypass capacitors with typical value 0.1 μF and 10 μF are applied to the supply rail for increasing stability. Nevertheless, these capacitors do not eliminate the need for bypassing of the LM48413 supply pins.

Input Capacitor Selection

Input capacitors may be required for some applications, or when the audio source is single-ended. Input capacitors block the DC component of the audio signal, eliminating any conflict between the DC component of the audio source and the bias voltage of the LM48413. The input capacitors create a high-pass filter with the input resistance R_{IN} . The -3dB point of the high-pass filter is found using Equation 1 below.

$$f = 1 / 2\pi R_{IN} C_{IN} \quad (\text{Hz}) \quad (1)$$

The input capacitors can also be used to remove low frequency content from the audio signal. When the LM48413 is using a single-ended source, power supply noise on the ground is seen as an input signal. Setting the high-pass filter point above the power supply noise frequencies, 217Hz in a GSM phone, for example, filters out the noise such that it is not amplified and heard on the output. Capacitors with a tolerance of 10% or better are recommended for impedance matching and improved CMRR and PSRR.

National 3D Enhancement

The LM48413 features National's 3D enhancement effect that widens the perceived soundstage of a stereo audio signal. The 3D enhancement increases the apparent stereo channel separation, improving audio reproduction whenever the left and right speakers are too close to one another.

An external RC network shown in Figure 1 is required to enable the 3D effect. Because the LM48413 is a fully differential amplifier, there are two separate RC networks, one for each stereo input pair (INL+ and INR+, and INL- and INR-). Set 3DEN high to enable the 3D effect. Set 3DEN low to disable the 3D effect.

The 3D RC network acts as a high-pass filter. The amount of the 3D effect is set by the R_{3D} resistor. Decreasing the value of R_{3D} increases the 3D effect. The C_{3D} capacitor sets the frequency at which the 3D effect occurs. Increasing the value of C_{3D} decreases the low frequency cutoff point, extending the 3D effect over a wider bandwidth. The low frequency cut-off point is given by Equation 2:

$$f_{3D(-3dB)} = 1 / 2\pi(R_{3D})(C_{3D}) \quad (\text{Hz}) \quad (2)$$

Enabling the 3D effect increase the gain by a factor of $(1 + 40k\Omega/R_{3D})$. Setting R_{3D} to $40k\Omega$ results in a gain increase of

6dB whenever the 3D effect is enabled. The Equation (2) holds for both differential and single-end configuration. The recommended tolerance of the resistor value and capacitor value of the two RC networks are 5% and 10% respectively. Tolerance out of this range may affect the 3D gain and low frequency cut-off point too much. The desired sound quality of the 3D effect may not be obtained consequently.

SINGLE-ENDED AUDIO AMPLIFIER CONFIGURATION

The LM48413 is compatible with single-ended sources. When configured for single-ended inputs, input capacitors must be used to block and DC component at the input of the device. Figure 2 shows the typical single-ended applications circuit.

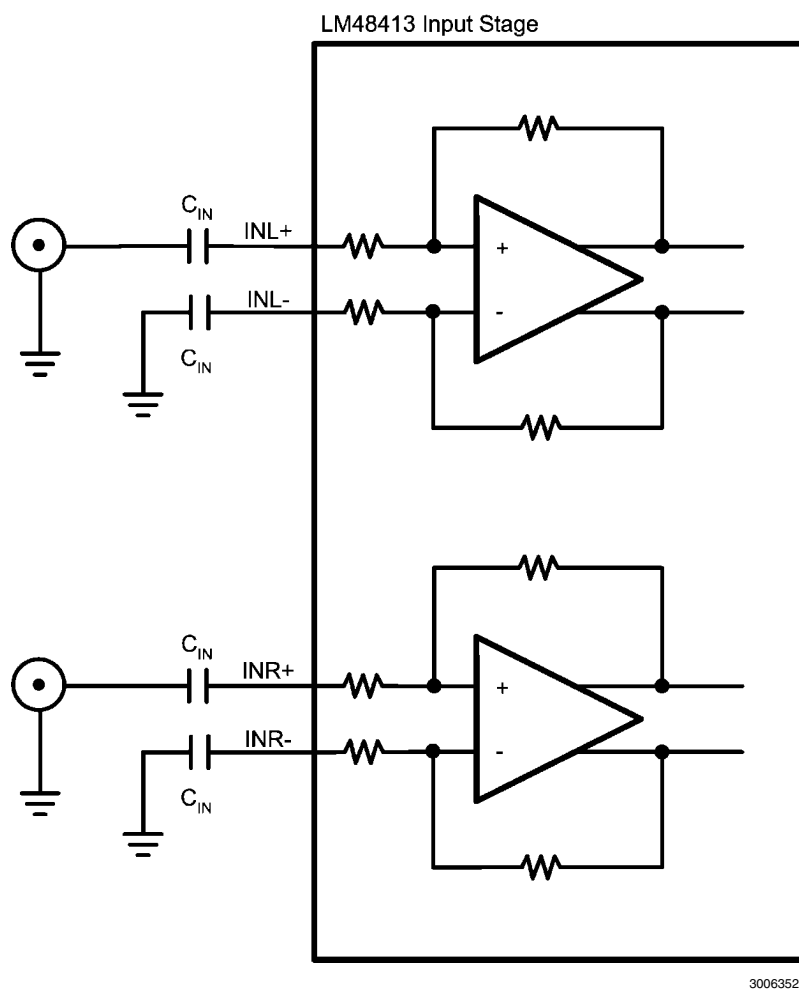


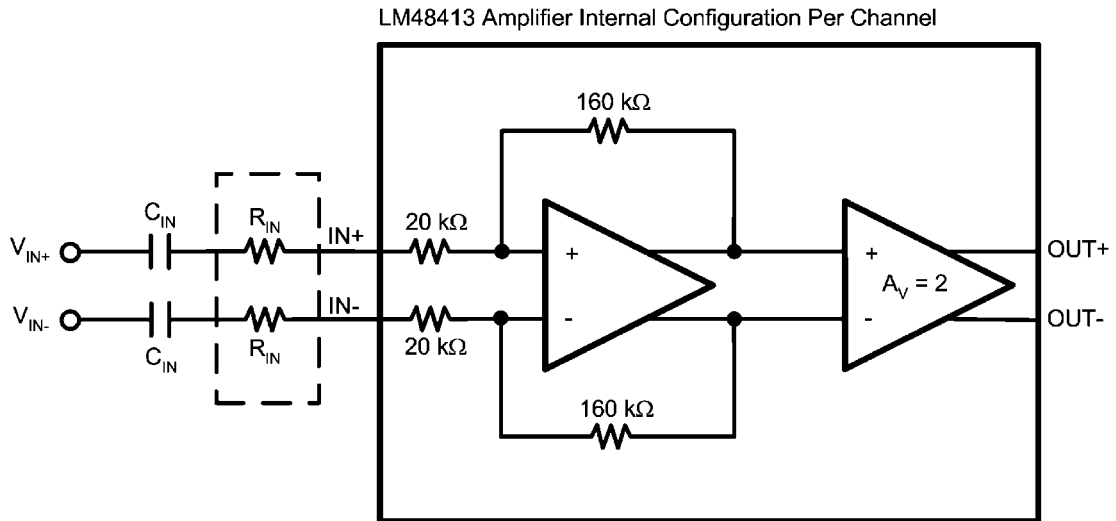
FIGURE 2. Single-Ended Circuit Diagram

AUDIO AMPLIFIER GAIN

The LM48413 has a fix gain value 24dB which is suitable for ordinary audio applications. To reduce the amplifier gain, insert two pairs of external input resistors with same value before the IC's input signal pins. Figure 3 show the configuration of these input resistors and the amplifier's internal gain setting. Accordingly, the overall amplifier gain is given by Equation 3:

$$A_V = 2 * (160k) / (20k + R_{IN}) \quad (3)$$

For example, if the gain to be set is 12dB, then A_V is equal to 4. Thus, Equation (3) the input resistors' value $R_{IN} = [(2 * 160k)/4] - 20k = 60k\Omega$.



30063528

FIGURE 3. Audio Amplifier Gain Setting

PCB LAYOUT GUIDELINES

As output power increases, interconnect resistance (PCB traces and wires) between the amplifier, load and power supply create a voltage drop. The voltage loss due to the traces between the LM48413 and the load results in lower output power and decreased efficiency. Higher trace resistance between the supply and the LM48413 has the same effect as a poorly regulated supply, increasing ripple on the supply line, and reducing peak output power. The effects of residual trace resistance increases as output current increases due to higher output power, decreased load impedance or both. To maintain the highest output voltage swing and corresponding peak output power, the PCB traces that connect the output pins to the load and the supply pins to the power supply should be as wide as possible to minimize trace resistance.

The use of power and ground planes will give the best THD+N performance. In addition to reducing trace resistance, the use of power planes creates parasitic capacitors that help to filter the power supply line.

The inductive nature of the transducer load can also result in overshoot on one or both edges, clamped by the parasitic diodes to GND and V_{DD} in each case. From an EMI standpoint, this is an aggressive waveform that can radiate or conduct to other components in the system and cause interference. It is essential to keep the power and output traces short and well shielded if possible. Use of ground planes beads and micro-strip layout techniques are all useful in preventing unwanted interference.

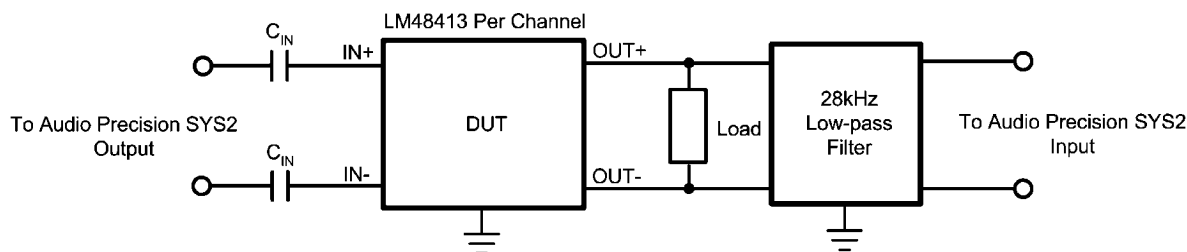
As the distance from the LM48413 and the speaker increases, the amount of EMI radiation increases due to the output wires

or traces acting as antennas. The EMI output spectrums of LM48413 evaluation board connected with different speaker cable lengths to an 8Ω load were measured (See Typical Performance Characteristics). Lengths from 3 inches to 12 inches are shown all fall within the limit of the FCC Class B requirement.

THD+N MEASUREMENT

Class D amplifiers, by design, switch their output power devices at a much higher frequency than the accepted audio range (20Hz – 22kHz). Alternately switching the output voltage between V_{DD} and GND allows the LM48413 to operate at much higher efficiency. However, it also increases the out-of-band noise. Since THD+N measurement is a bandwidth limited measurement, it can be significantly affected by out-of-band noise, resulting in a higher than expected THD+N measurement. To achieve a more accurate measurement of THD+N, the test equipment's input bandwidth must be limited. The input filter limits the out-of-band noise resulting in a more relevant THD+N value. A low-pass filter with a cut-off at 28kHz was used in addition to the internal filter of the THD+N measurement equipment (See Figure 4).

In real applications, the output filters are not necessary since the speakers will act as low-pass filters blocking the remaining switching noise and smoothing the output signals. Instead of connecting the LM48413's BTL outputs to speakers during measurements, the 28kHz low-pass filter is used as shown in Figure 4. This measurement technique also applies to measurements such as PSRR, CMRR, and output power.



30063540

FIGURE 4. THD+N Measurement Test Setup

Bill Of Materials

TABLE 1. LM48413 Demonstration Board Bill of Materials

Item	Designator	Description	Part Number	Qty	Value	Recommended Supplier
1	U1	Stereo Class-D	LM48413TL	1		National Semiconductor
2	R1, R2	Resistor (0603)		2	4.7k Ω \pm 5%	Towa
3	C1, C2, C3, C8	Ceramic Capacitor (0603) X7R	GRM188R71C105KA01D	4	1 μ F \pm 10%, 25V	Murata
4	C4, C5, C6, C7	Ceramic Capacitor (1206) X7R	C3216X741H105K	4	1 μ F \pm 10%, 25V	TDK
5	C9	Tantium Capacitor (1210)	594D106X0025B2T	1	10 μ F \pm 10%, 25V	Vishay
6	JP5, JP6, JP7	Header 2-pin		3		
7	JP1, JP2	Header 3-pin		2		
8	JP3, JP4	Header 4-pin		2		
9	R3, R4	Potentiometer	ST-4EB100k	2	100k Ω	Copal Electronics

Demonstration Board Schematic

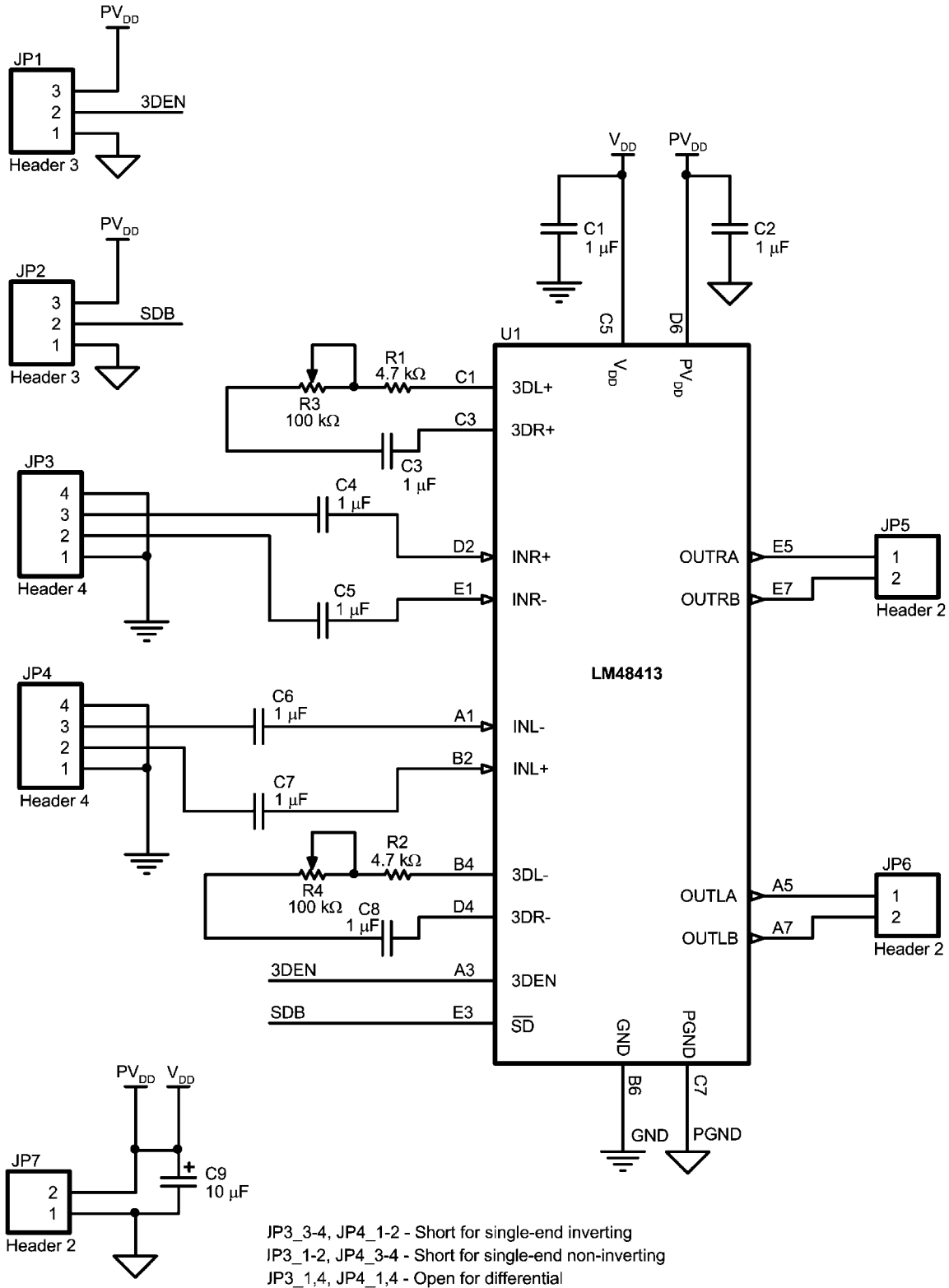
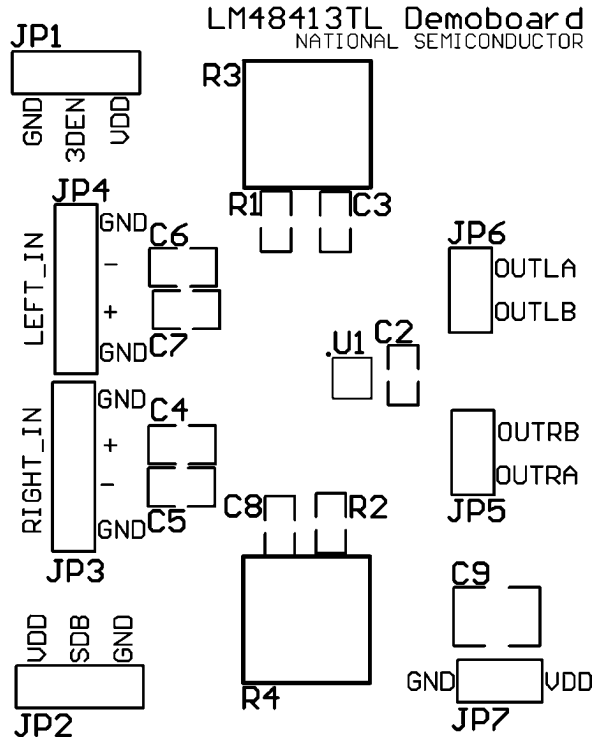


FIGURE 5. LM48413 Demonstration Board Schematic

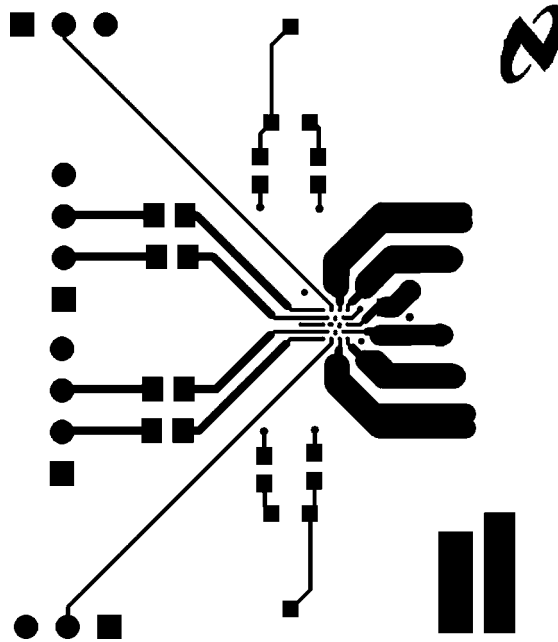
30063510

Demonstration Board Layout



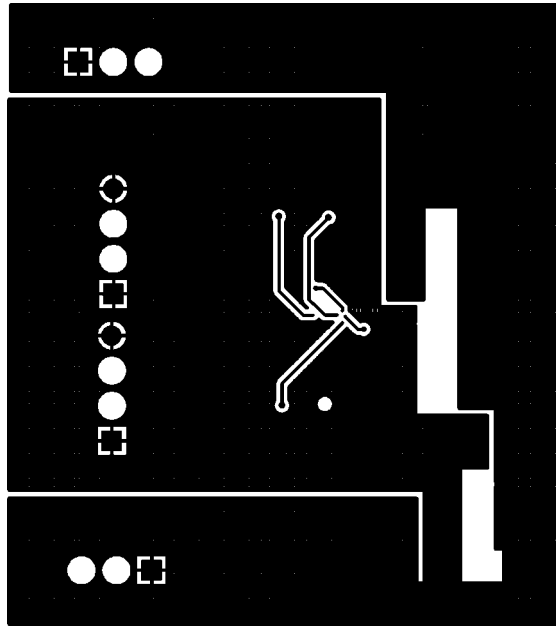
30063511

Top Silkscreen



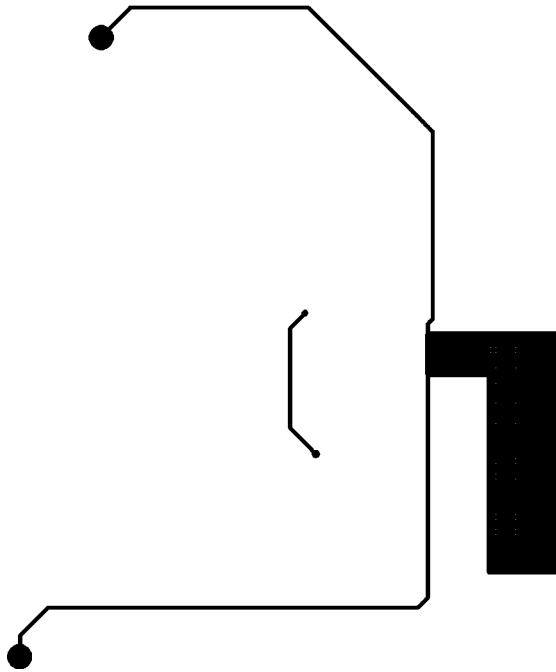
30063515

Top Layer



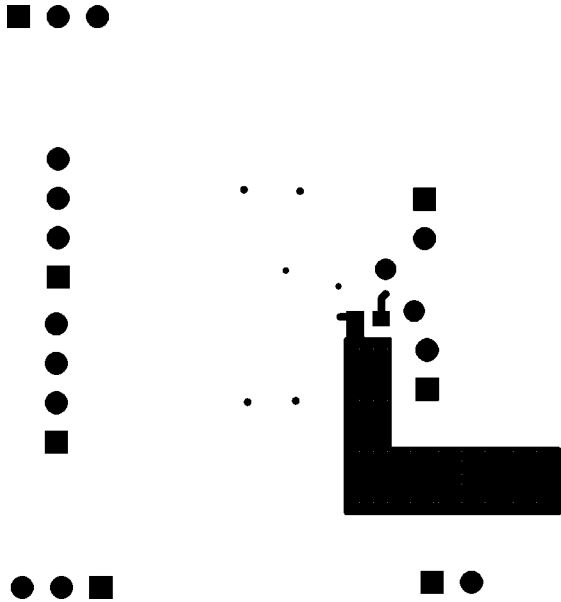
Middle Layer 1

30063513



Middle Layer 2

30063514



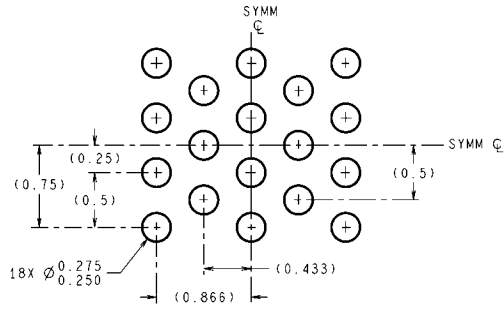
Bottom Layer

30063512

Revision Table

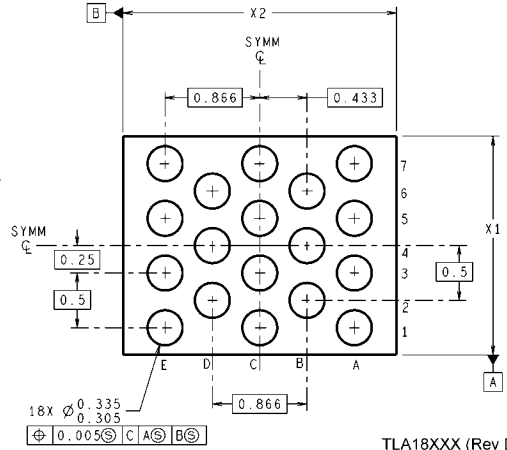
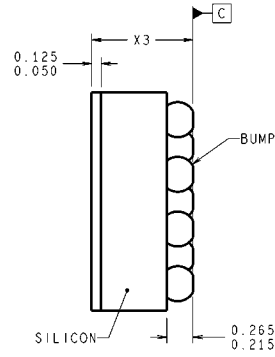
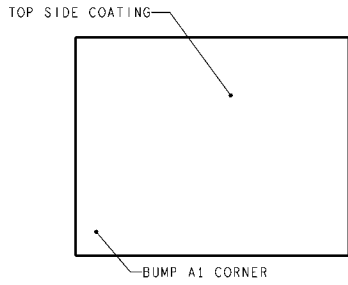
Rev	Date	Description
1.0	11/19/08	Initial release.
1.01	01/08/09	Text edits.

Physical Dimensions inches (millimeters) unless otherwise noted



DIMENSIONS ARE IN MILLIMETERS
DIMENSIONS IN () FOR REFERENCE ONLY

LAND PATTERN RECOMMENDATION



TLA18XXX (Rev D)

MicroSMD 18 Bump Package
Order Number LM48413TL, LM48413TLX
NS Package Number TLA18CBA
X₁ = 2.047mm ±0.030mm X₂ = 2.250mm ±0.030mm X₃ = 0.60mm ±0.075mm

Notes

LM48413

Notes

For more National Semiconductor product information and proven design tools, visit the following Web sites at:

Products		Design Support	
Amplifiers	www.national.com/amplifiers	WEBENCH® Tools	www.national.com/webench
Audio	www.national.com/audio	App Notes	www.national.com/appnotes
Clock and Timing	www.national.com/timing	Reference Designs	www.national.com/refdesigns
Data Converters	www.national.com/adc	Samples	www.national.com/samples
Interface	www.national.com/interface	Eval Boards	www.national.com/evalboards
LVDS	www.national.com/lvds	Packaging	www.national.com/packaging
Power Management	www.national.com/power	Green Compliance	www.national.com/quality/green
Switching Regulators	www.national.com/switchers	Distributors	www.national.com/contacts
LDOs	www.national.com/ldo	Quality and Reliability	www.national.com/quality
LED Lighting	www.national.com/led	Feedback/Support	www.national.com/feedback
Voltage Reference	www.national.com/vref	Design Made Easy	www.national.com/easy
PowerWise® Solutions	www.national.com/powerwise	Solutions	www.national.com/solutions
Serial Digital Interface (SDI)	www.national.com/sdi	Mil/Aero	www.national.com/milaero
Temperature Sensors	www.national.com/tempsensors	Solar Magic®	www.national.com/solarmagic
Wireless (PLL/VCO)	www.national.com/wireless	Analog University®	www.national.com/AU

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2009 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Technical Support Center
 Email: support@nsc.com
 Tel: 1-800-272-9959

National Semiconductor Europe Technical Support Center
 Email: europe.support@nsc.com
 German Tel: +49 (0) 180 5010 771
 English Tel: +44 (0) 870 850 4288

National Semiconductor Asia Pacific Technical Support Center
 Email: ap.support@nsc.com

National Semiconductor Japan Technical Support Center
 Email: jpn.feedback@nsc.com